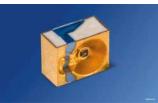
Engwinklige LED im MIDLED-Gehäuse Narrow beam LED in MIDLED package Lead (Pb) Free Product - RoHS Compliant

SFH 4640 SFH 4645





SFH 4640

SFH 4645

Wesentliche Merkmale

- Infrarot LED mit hoher Ausgangsleistung (45 mW)
- Emissionswellenlänge typ. 940 nm
- Enger Abstrahlwinkel (± 15°)
- · Geringe Bauhöhe
- Als Toplooker und Sidelooker einsetzbar
- SFH 4640: Gurtung als Toplooker SFH 4645: Gurtung als Sidelooker

Anwendungen

- Infrarotbeleuchtung für Kameras
- IR-Datenübertragung
- Sensorik in der Automobiltechnik
- Fernsteuerung

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

Features

- High Power (45 mW) Infrared LED
- · Peak wavelength typ. 940 nm
- Narrow halfangle (± 15°)
- Low profile component
- · Usable as top-looking and side-looking device
- SFH 4640: Taping as Toplooker SFH 4645: Taping as Sidelooker

Applications

- Infrared Illumination for cameras
- · IR Data Transmission
- · Automotive sensors
- · Remote controls

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Typ Type	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$) Radiant Intensity Grouping ¹⁾ $I_e \text{ (mW/sr)}$
SFH 4640	Q65110A9369	≥ 25 (typ. 60)
SFH 4645	Q65110A9367	≥ 25 (typ. 60)

¹⁾ gemessen bei einem Raumwinkel Ω = 0.01 sr / measured at a solid angle of Ω = 0.01 sr

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Grenzwerte ($T_{\rm A}$ = 25 °C) Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{ m op}$, $T_{ m stg}$	- 40 + 100	°C
Sperrspannung Reverse voltage	V_{R}	5	V
Vorwärtsgleichstrom Forward current	I_{F}	100	mA
Stoßstrom, $t_p = 300 \mu s$, $D = 0$ Surge current	I_{FSM}	1	A
Verlustleistung Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm² Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 16 mm² each Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	$R_{ m thJA}$ $R_{ m thJS}$	180	K/W

Kennwerte (T_A = 25 °C) Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_{\rm F} = 100 \; {\rm mA}$	λ_{peak}	950	nm
Centroid-Wellenlänge der Strahlung Centroid wavelength $I_{\rm F}$ = 100 mA	$\lambda_{centroid}$	940	nm
Spektrale Bandbreite bei 50% von $I_{\rm max}$ Spectral bandwidth at 50% of $I_{\rm max}$ $I_{\rm F}$ = 100 mA	Δλ	42	nm
Abstrahlwinkel Half angle	φ	± 15	Grad deg.

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Kennwerte ($T_A = 25$ °C) Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3 × 0.3	mm²
Schaltzeiten, $I_{\rm e}$ von 10% auf 90% und von 90% auf 10%, bei $I_{\rm F}$ = 100 mA, $R_{\rm L}$ = 50 Ω Switching times, $I_{\rm e}$ from 10% to 90% and from 90% to 10%, $I_{\rm F}$ = 100 mA, $R_{\rm L}$ = 50 Ω	$t_{\rm r},t_{\rm f}$	11	ns
Durchlassspannung Forward voltage $I_{\rm F}$ = 100 mA, $t_{\rm p}$ = 20 ms $I_{\rm F}$ = 1 A, $t_{\rm p}$ = 100 μ s	V_{F} V_{F}	1.5 (< 1.8) 2.3 (< 3.0)	V V
Sperrstrom Reverse current	I_{R}	not designed for reverse operation	μΑ
Gesamtstrahlungsfluss Total radiant flux $I_{\rm F}$ = 100 mA, $t_{\rm p}$ = 20 ms	Φ _{e typ}	45	mW
Temperaturkoeffizient von $\rm I_e$ bzw. $\rm \Phi_e$, I_F = 100 mA Temperature coefficient of $\rm I_e$ or $\rm \Phi_e$, I_F = 100 mA	TC ₁	- 0.5	%/K
Temperaturkoeffizient von $V_{\rm F},I_{\rm F}$ = 100 mA Temperature coefficient of $V_{\rm F},I_{\rm F}$ = 100 mA	TC_{\vee}	-3	mV/K
Temperaturkoeffizient von λ , $I_{\rm F}$ = 100 mA Temperature coefficient of λ , $I_{\rm F}$ = 100 mA	TC_{λ}	+ 0.3	nm/K

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Strahlstärke I_e in Achsrichtung¹⁾

gemessen bei einem Raumwinkel $\Omega = 0.01$ sr

Radiant Intensity Ie in Axial Direction

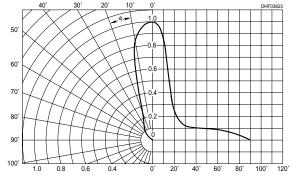
at a solid angle of $\Omega = 0.01 \text{ sr}$

Bezeichnung Parameter	Symbol	Werte Values		Einheit Unit	
		-T	-U	-V	
Strahlstärke Radiant intensity $I_{\rm F} = 100$ mA, $t_{\rm p} = 20$ ms	$I_{\text{e min}} \\ I_{\text{e max}}$	25 50	40 80	63 125	mW/sr mW/sr
Strahlstärke Radiant intensity $I_{\rm F} = 1 \text{ A}, t_{\rm p} = 25 \mu\text{s}$	I _{e typ}	260	420	660	mW/sr

¹⁾ Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1) / Only one bin in one packing unit (variation lower 2:1)

Abstrahlcharakteristik

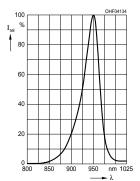
Radiation Characteristics $I_{rel} = f(\varphi)$



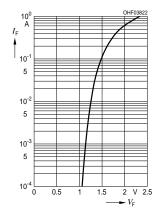
OSRAM

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Relative Spectral Emission $I_{\rm rel} = f(\lambda)$

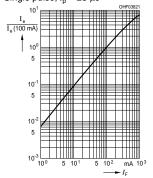


Forward Current $I_F = f(V_F)$ Single pulse, $t_D = 100 \mu s$

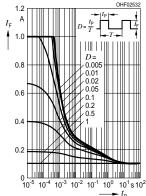


Radiant Intensity $\frac{I_e}{I_e \text{ 100 mA}} = f(I_F)$

Single pulse, $t_p = 25 \mu s$

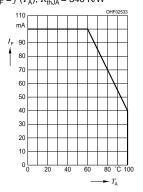


Permissible Pulse Handling Capability $I_{\rm F}$ = f (τ), $T_{\rm A}$ = 25 °C, duty cycle D = parameter



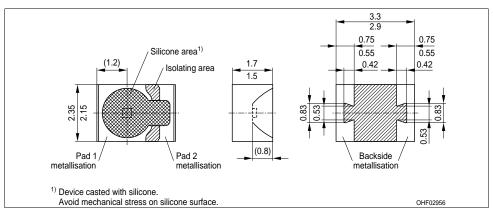
5

Max. Permissible Forward Current $I_{\rm F}$ = f ($T_{\rm A}$), $R_{\rm thJA}$ = 340 K/W



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Maßzeichnung Package Outlines



Maße in mm / Dimensions in mm.

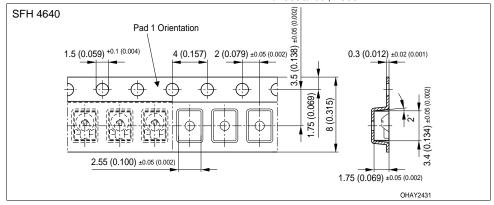
Gehäuse / Package	MID mit klarem Silikonverguss / MID casted with clear Silicone
Anschlussbelegung	Pad 1 = Anode / anode
Pin configuration	Pad 2 = Kathode / cathode

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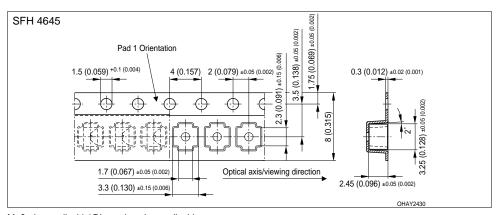
Gurtung / Polarität und Lage

Method of Taping / Polarity and Orientation

Verpackungseinheit 2000/Rolle, ø180 mm oder 9000/Rolle, ø330 mm Packing unit 2000/reel, ø180 mm or 9000/reel, ø330 mm



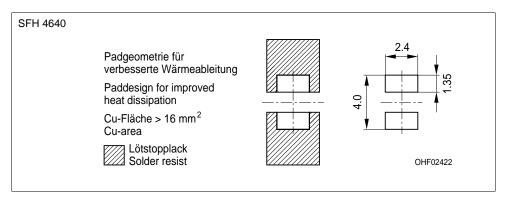
Maße in mm (inch) / Dimensions in mm (inch).

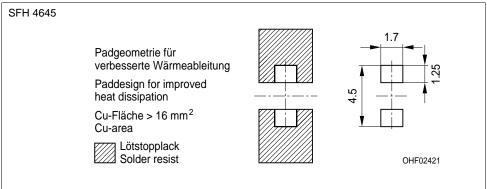


Maße in mm (inch) / Dimensions in mm (inch).



Empfohlenes Lötpaddesign Recommended Solder Pad Design





Maße in mm / Dimensions in mm.

Verarbeitungshinweis: Das Gehäuse ist mit Silikon vergossen. Mechanischer Stress auf der

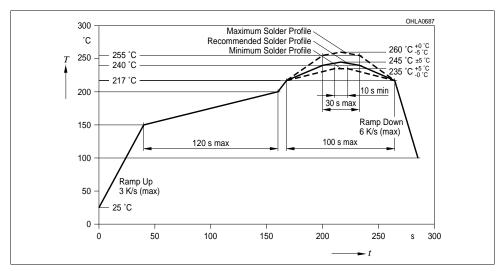
Bauteiloberfläche sollte so gering wie möglich gehalten werden.

Handling indication: The package is casted with silicone. Mechanical stress at the surface of

the unit should be as low as possible.



Lötbedingungen Soldering Conditions Reflow Lötprofil für bleifreies Löten Reflow Soldering Profile for lead free soldering Vorbehandlung nach JEDEC Level 2 Preconditioning acc. to JEDEC Level 2 (nach J-STD-020C) (acc. to J-STD-020C)



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